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RLT904-10G TECHNICAL DATA



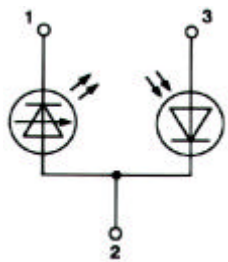
High Power Infrared Laserdiode

Structure: **GaAlAs double heterostructure**
 Lasing wavelength: **904 nm typ., singlemode**
 Max. optical power: **10 mW**
 Package: **9 mm**

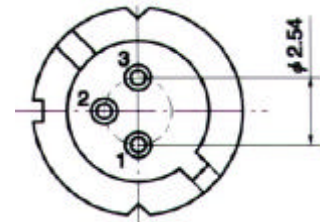
NOTE!
 LASERDIODE
 MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	25	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operating Temperature	T _C	-60 .. +60	°C
Storage Temperature	T _{STG}	-70 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I _{th}	cw	100	130	170	mA
Operation Current	I _{op}	P _o = 10 mW		160	180	mA
Operation Voltage	U _{op}	P _o = 10 mW		2.2		V
Lasing Wavelength	λ _p	P _o = 10 mW	890	904	910	nm
Beam Divergence	θ _{//}	P _o = 10 mW	7	10	13	°
Beam Divergence	θ _⊥	P _o = 10 mW	15	30	35	°
Monitor Current	I _m	P _o = 10 mW	0.6	1	1.2	mA